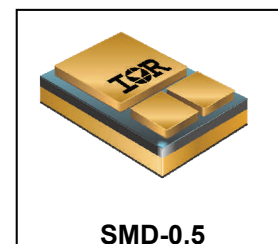


**HEXFET® POWER MOSFET
SURFACE MOUNT (SMD-0.5)**

150V, P-CHANNEL

Product Summary

| Part Number | BV_{DSS} | $R_{DS(on)}$ | I_D |
|-------------|------------|--------------|-------|
| IRF5NJ6215 | -150V | 0.29Ω | -11A |



Description

Fifth Generation HEXFET® power MOSFETs from IR HiRel utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon unit area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

These devices are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high-energy pulse circuits.

Features

- Low $R_{DS(on)}$
- Avalanche Energy Ratings
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Hermetically Sealed
- Surface Mount
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

| Symbol | Parameter | Value | Units |
|---|---|---------------|-------|
| $I_{D1} @ V_{GS} = -10V, T_C = 25^\circ C$ | Continuous Drain Current | -11 | A |
| $I_{D2} @ V_{GS} = -10V, T_C = 100^\circ C$ | Continuous Drain Current | -7.2 | |
| $I_{DM} @ T_C = 25^\circ C$ | Pulsed Drain Current ① | -44 | |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 75 | W |
| | Linear Derating Factor | 0.6 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ±20 | V |
| E_{AS} | Single Pulse Avalanche Energy ② | 130 | mJ |
| I_{AR} | Avalanche Current ① | -11 | A |
| E_{AR} | Repetitive Avalanche Energy ① | 7.5 | mJ |
| dv/dt | Peak Diode Recovery dv/dt ③ | 10 | V/ns |
| T_J T_{STG} | Operating Junction and Storage Temperature Range | -55 to + 150 | °C |
| | Package Mounting Surface Temp | 300 (for 5s) | |
| | Weight | 1.0 (Typical) | g |

For Footnotes, refer to the page 2.

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

| Symbol | Parameter | Min. | Typ. | Max. | Units | Test Conditions |
|-------------------------------------|--------------------------------------|------|-------|------|-------|---|
| BV _{DSS} | Drain-to-Source Breakdown Voltage | -150 | — | — | V | V _{GS} = 0V, I _D = -250μA |
| ΔBV _{DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | -0.17 | — | V/°C | Reference to 25°C, I _D = -1.0mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | — | 0.29 | Ω | V _{GS} = -10V, I _{D2} = -7.2A ④ |
| V _{GS(th)} | Gate Threshold Voltage | -2.0 | — | -4.0 | V | V _{DS} = V _{GS} , I _D = -250μA |
| g _{fs} | Forward Transconductance | 2.3 | — | — | S | V _{DS} = -25V, I _{D2} = -7.2A ④ |
| I _{DSS} | Zero Gate Voltage Drain Current | — | — | -25 | μA | V _{DS} = -120V, V _{GS} = 0V |
| | | — | — | -250 | | V _{DS} = -120V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Leakage Forward | — | — | -100 | nA | V _{GS} = -20V |
| | Gate-to-Source Leakage Reverse | — | — | 100 | | V _{GS} = 20V |
| Q _G | Total Gate Charge | — | — | 66 | nC | I _{D2} = -7.2A |
| Q _{GS} | Gate-to-Source Charge | — | — | 13 | | V _{DS} = -120V |
| Q _{GD} | Gate-to-Drain ('Miller') Charge | — | — | 40 | | V _{GS} = -10V |
| t _{d(on)} | Turn-On Delay Time | — | — | 25 | ns | V _{DD} = -75V |
| t _r | Rise Time | — | — | 65 | | I _{D2} = -7.2A |
| t _{d(off)} | Turn-Off Delay Time | — | — | 75 | | R _G = 6.8Ω |
| t _f | Fall Time | — | — | 53 | | V _{GS} = -10V |
| L _S + L _D | Total Inductance | — | 4.0 | — | nH | Measured from center of Drain pad to center of Source pad |
| C _{iss} | Input Capacitance | — | 990 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 230 | — | | V _{DS} = -25V |
| C _{rss} | Reverse Transfer Capacitance | — | 120 | — | | f = 1.0MHz |

Source-Drain Diode Ratings and Characteristics

| Symbol | Parameter | Min. | Typ. | Max. | Units | Test Conditions |
|-----------------|--|---|------|------|-------|---|
| I _S | Continuous Source Current (Body Diode) | — | — | -11 | A | |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | -44 | | |
| V _{SD} | Diode Forward Voltage | — | — | -1.6 | V | T _J = 25°C, I _S = -7.2A, V _{GS} = 0V ④ |
| t _{rr} | Reverse Recovery Time | — | — | 240 | ns | T _J = 25°C, I _F = -7.2A, V _{DD} ≤ -25V |
| Q _{rr} | Reverse Recovery Charge | — | — | 1.7 | μC | di/dt = -100A/μs ④ |
| t _{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by L _S + L _D) | | | | |

Thermal Resistance

| Symbol | Parameter | Min. | Typ. | Max. | Units |
|------------------|------------------|------|------|------|-------|
| R _{θJC} | Junction-to-Case | — | — | 1.67 | °C/W |

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② V_{DD} = -50V, starting T_J = 25°C, L = 5.0mH, Peak I_L = -7.2A, V_{GS} = -10V, R_G = 25Ω
- ③ I_{SD} ≤ -7.2A, di/dt ≤ -390A/μs, V_{DD} ≤ -150V, T_J ≤ 150°C
- ④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%

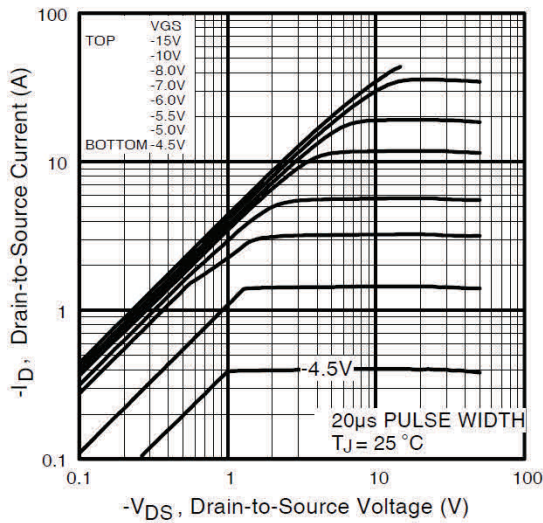


Fig 1. Typical Output Characteristics

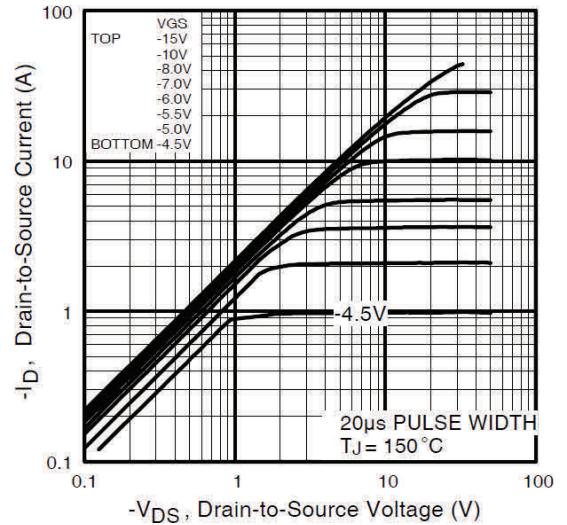


Fig 2. Typical Output Characteristics

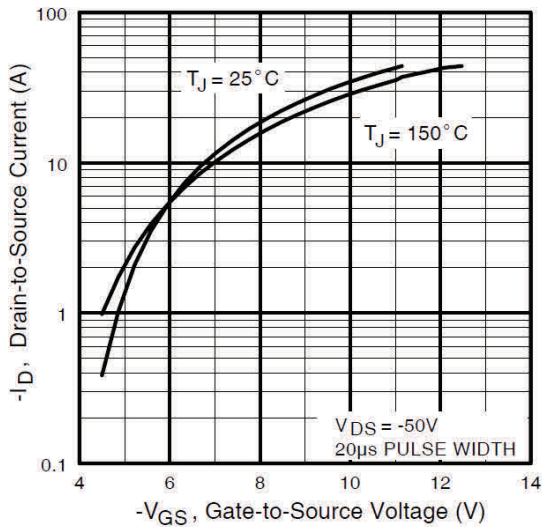


Fig 3. Typical Transfer Characteristics

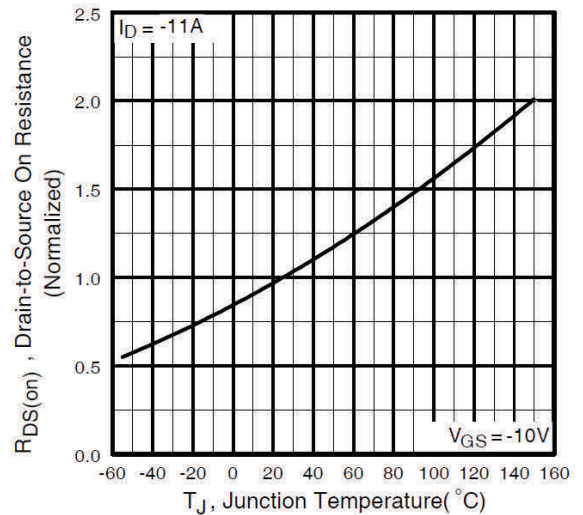


Fig 4. Normalized On-Resistance Vs. Temperature

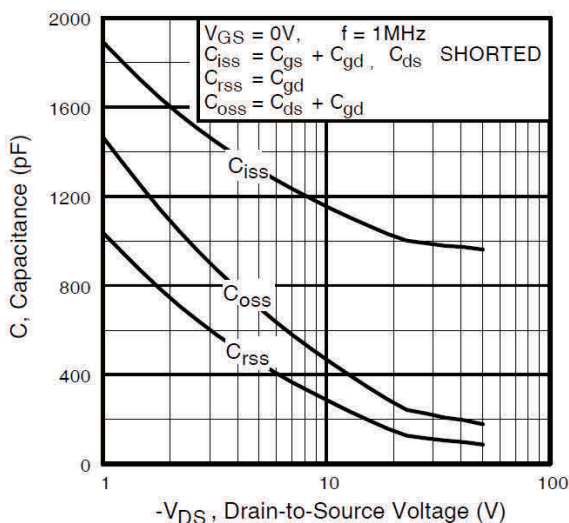


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

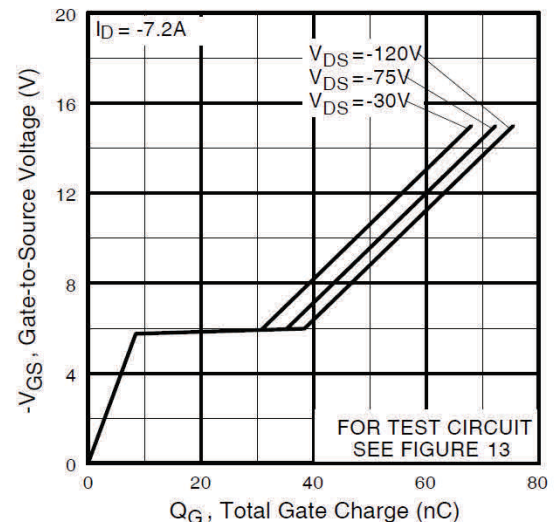


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

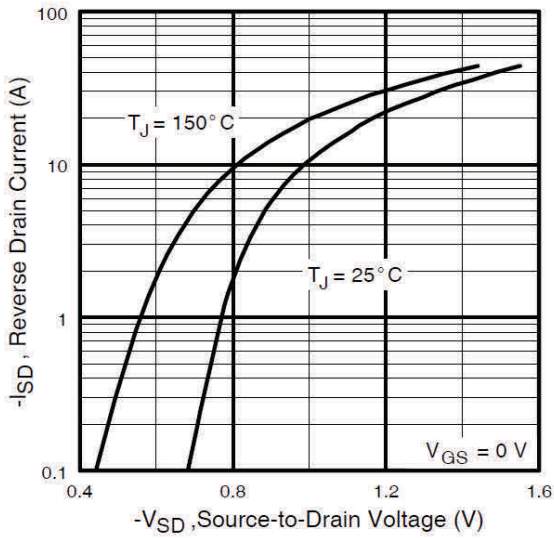


Fig 7. Typical Source-Drain Diode Forward Voltage

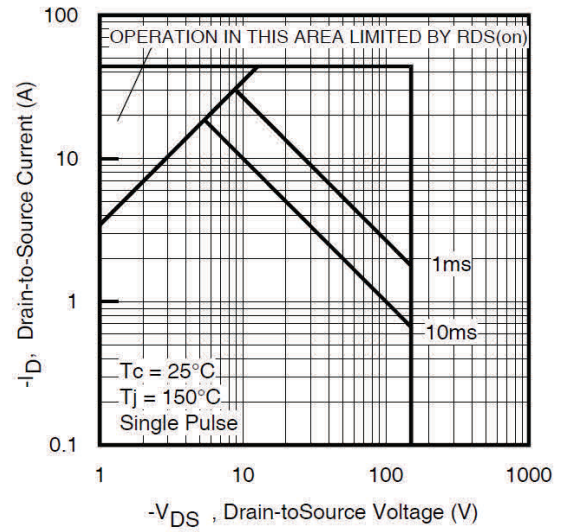


Fig 8. Maximum Safe Operating Area

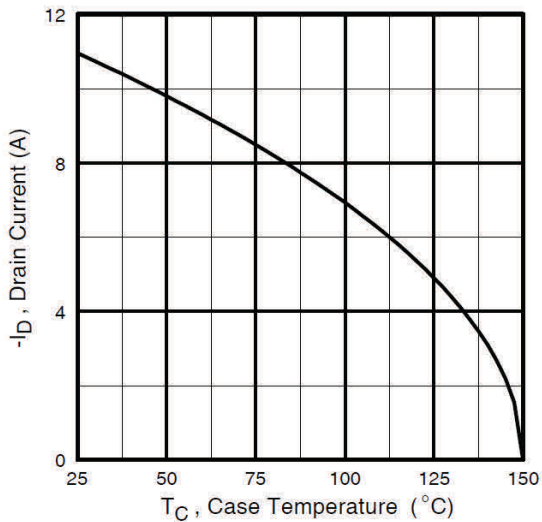


Fig 9. Maximum Drain Current Vs. Case Temperature

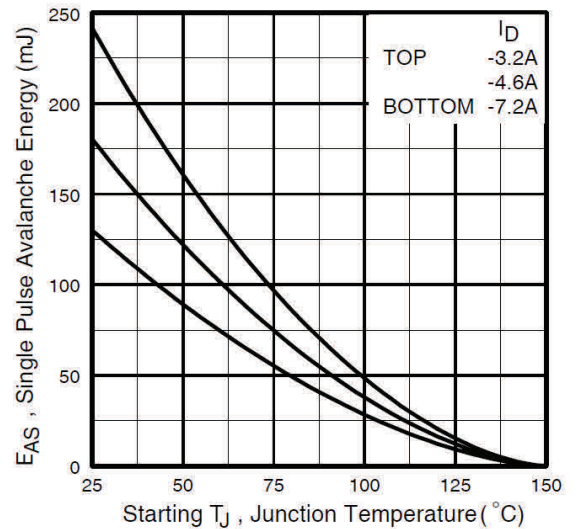


Fig 10. Maximum Avalanche Energy Vs. Drain Current

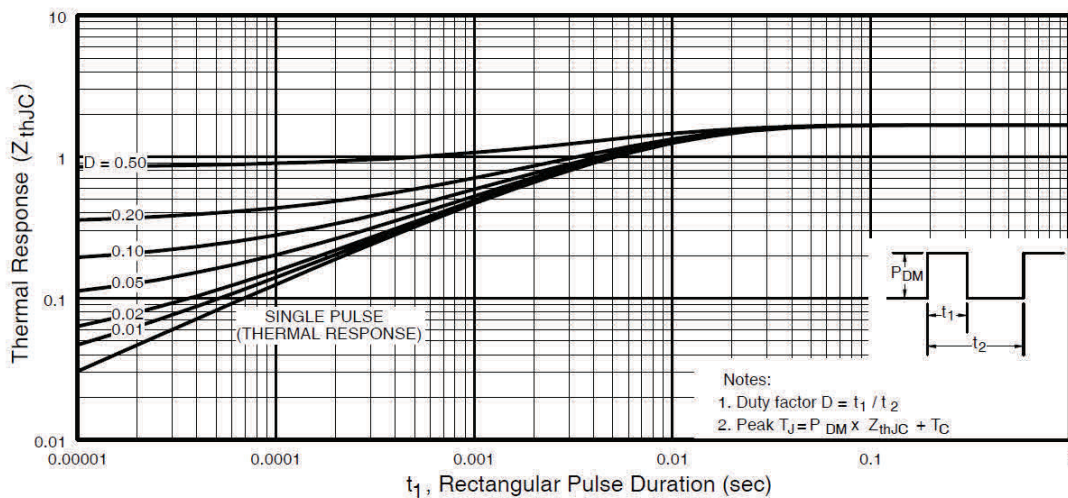


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

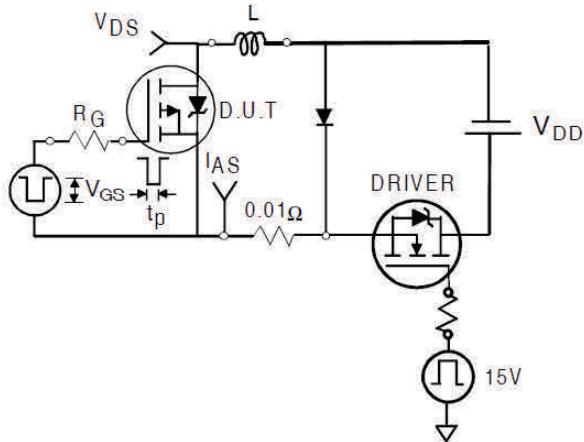


Fig 12a. Unclamped Inductive Test Circuit

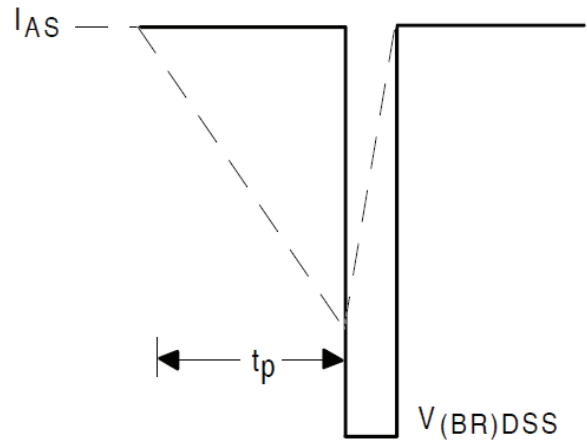


Fig 12b. Unclamped Inductive Waveforms

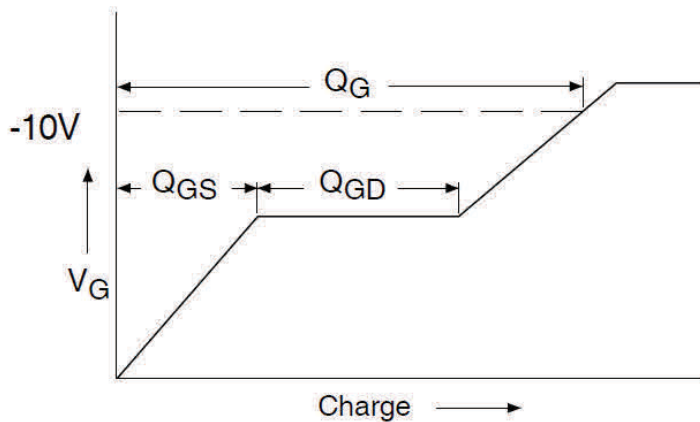


Fig 13a. Gate Charge Waveform

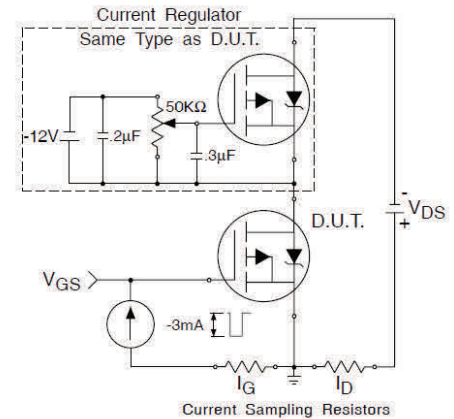


Fig 13b. Gate Charge Test Circuit

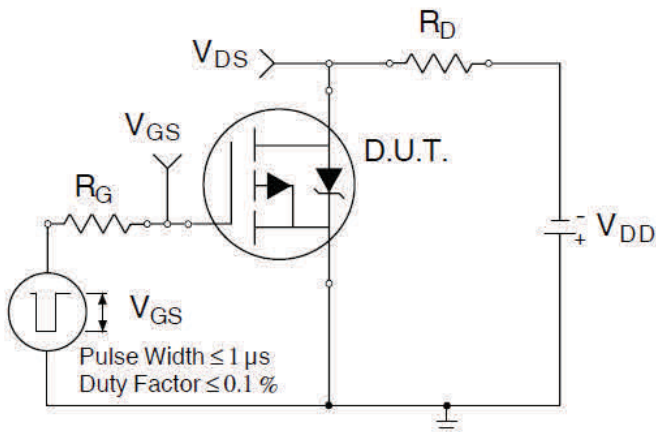


Fig 14a. Switching Time Test Circuit

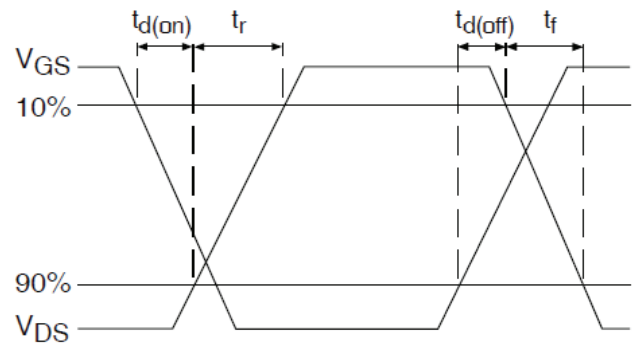
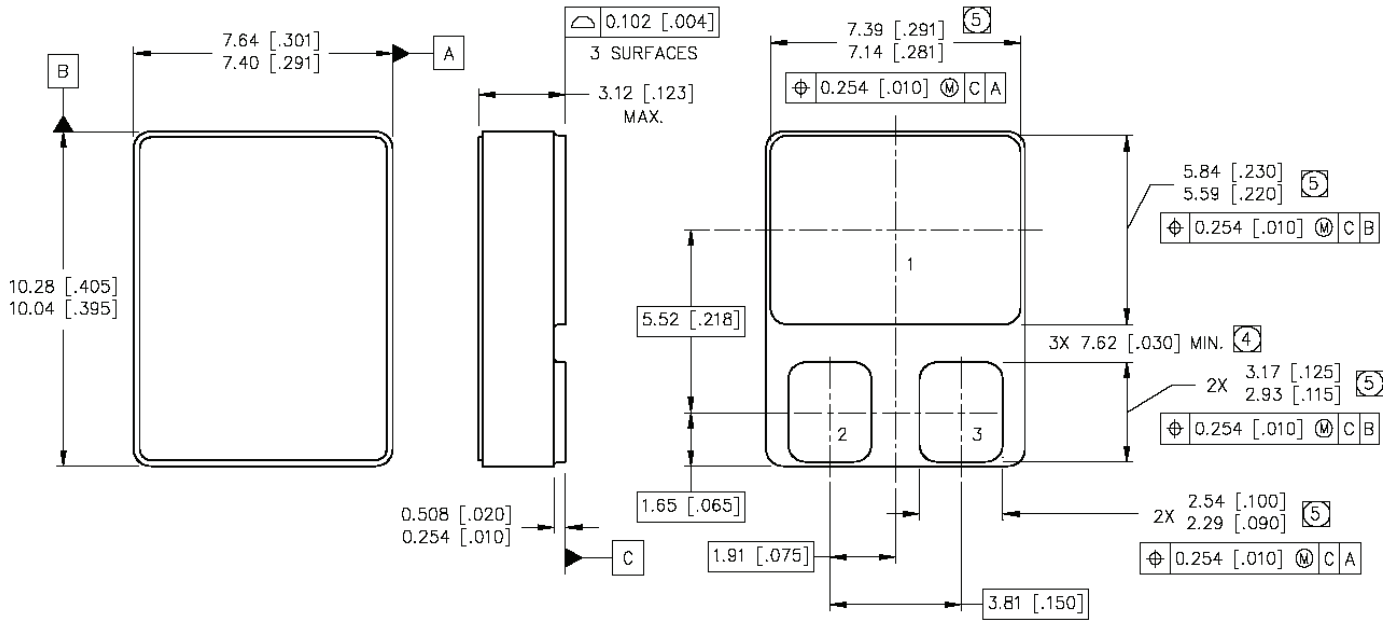


Fig 14b. Switching Time Waveforms

Case Outline and Dimensions — SMD-0.5



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- ④ DIMENSION INCLUDES METALLIZATION FLASH.
- ⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

- 1 = DRAIN
- 2 = GATE
- 3 = SOURCE

IMPORTANT NOTICE

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